

Radiation Effects in Silicon Carbide

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Summary:

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Further, the possibility to produce controlled transformation of silicon carbide polytype is considered. The involvement of radiation defects in radiative and nonradiative recombination processes in SiC is analyzed.

Data are also presented regarding the degradation of particular SiC electronic devices under the influence of radiation and a conclusion is made regarding the radiation resistance of SiC. Lastly, the radiation hardness of devices based on silicon and silicon carbide are compared.

